

Title (en)

A METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE FOR FORMING A DEEP FIELD REGION IN A SEMICONDUCTOR SUBSTRATE

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Application

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Priority

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Abstract (en)

[origin: US4532696A] This invention provides a method of forming a buried element isolation region in a semiconductor substrate. The method comprises steps of forming a gate electrode material pattern on a gate insulating film formed on a semiconductive substrate, forming a gate electrode by selectively forming a groove in said gate electrode material pattern to thereby isolate said pattern and burying insulating material in the groove.

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GB 1186625 A 19700402 - PHILCO FORD CORP [US]

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EP0115131A3; EP0091984A3; EP0618616A3; EP0195460A3; EP0818815A1; US6069055A; KR100844228B1; FR2568723A1; WO8601336A1

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